

Silicon NPN Power Transistors

2SC5802

DESCRIPTION

- With TO-3P(H)IS package
- High voltage;high speed
- Wide area of safe operation

APPLICATIONS

- For high voltage color display horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

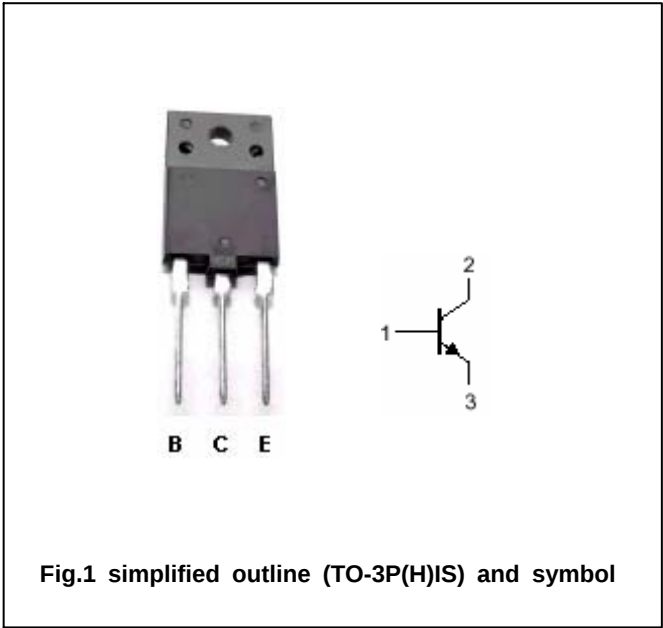


Fig.1 simplified outline (TO-3P(H)IS) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	800	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		10	A
I _{CM}	Collector current-Peak		30	A
P _C	Total power dissipation	T _C =25	60	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=6A$; $I_B=1.5A$			3.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=6A$; $I_B=1.5A$			1.5	V
I_{CES}	Collector cut-off current	$V_{CE}=1400V$; $V_{BE}=0$			1.0	mA
I_{CBO}	Collector cut-off current	$V_{CB}=800V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=4V$; $I_C=0$			1.0	mA
h_{FE-1}	DC current gain	$I_C=1A$; $V_{CE}=5V$	15		48	
h_{FE-2}	DC current gain	$I_C=6A$; $V_{CE}=5V$	7		10	
t_f	Fall time	$V_{CC}=200V$; $I_C=6A$; $I_{B1}=1.2A$ $I_{B2}=-2.4A$; $R_L=33.3\Omega$		0.1	0.3	μs

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PACKAGE OUTLINE

